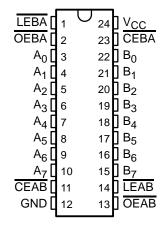
SCCS042C - SEPTEMBER 1994 - REVISED NOVEMBER 2001

- Function and Pinout Compatible With FCT and F Logic
- 25-Ω Output Series Resistors to Reduce Transmission-Line Reflection Noise
- Reduced V<sub>OH</sub> (Typically = 3.3 V) Versions of Equivalent FCT Functions
- Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Matched Rise and Fall Times
- Fully Compatible With TTL Input and Output Logic Levels
- 12-mA Output Sink Current
   15-mA Output Source Current
- Separation Controls for Data Flow in Each Direction
- Back-to-Back Latches for Storage
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)
- 3-State Outputs

#### Q OR SO PACKAGE (TOP VIEW)



## description

The CY74FCT2543T octal latched transceiver contains two sets of eight D-type latches. Separate latch enable (LEAB, LEBA) and output enable (OEAB, OEBA) inputs permit each latch set to have independent control of inputting and outputting in either direction of data flow. For example, for data flow from A to B, the A-to-B enable (CEAB) input must be low to enter data from A or to take data from B, as indicated in the function table. With CEAB low, a low signal on the A-to-B latch enable (LEAB) input makes the A-to-B latches transparent; a subsequent low-to-high transition of LEAB puts the A latches in the storage mode and their outputs no longer change with the A inputs. With CEAB and OEAB both low, the 3-state B output buffers are active and reflect data present at the output of the A latches. Control of data from B to A is similar, but uses CEAB, LEAB, and OEAB inputs. On-chip termination resistors at the outputs reduce system noise caused by reflections. The CY74FCT2543T can replace the CY74FCT543T to reduce noise in an existing design.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



#### **PIN DESCRIPTION**

NAME	DESCRIPTION
OEAB	A-to-B output-enable input (active low)
OEBA	B-to-A output-enable input (active low)
CEAB	A-to-B enable input (active low)
CEBA	B-to-A enable input (active low)
LEAB	A-to-B latch-enable input (active low)
LEBA	B-to-A latch-enable input (active low)
Α	A-to-B data inputs or B-to-A 3-state outputs
В	B-to-A data inputs or A-to-B 3-state outputs

## **ORDERING INFORMATION**

TA	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	QSOP – Q	Tape and reel	5.3	CY74FCT2543CTQCT	FCT2543C	
	SOIC - SO	Tube	5.3	CY74FCT2543CTSOC	FCT2543C	
	3010 - 30	Tape and reel	5.3	CY74FCT2543CTSOCT	FC12543C	
–40°C to 85°C	QSOP – Q	Tape and reel	6.5	CY74FCT2543ATQCT	FCT2543A	
	SOIC - SO	Tube	6.5	CY74FCT2543ATSOC	FCT2543A	
	3010 - 30	Tape and reel	6.5	CY74FCT2543ATSOCT	FC12543A	
	QSOP – Q	Tape and reel	8.5	CY74FCT2543TQCT	FCT2543	

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

## **FUNCTION TABLE**

	INPUTS		LATCH	OUTPUT
CEAB	LEAB	OEAB	А-ТО-В‡	В
Н	Х	Х	Storing	Z
Х	Н	X	Storing	X
Х	Χ	Н	X	Z
L	L	L	Transparent	Current A inputs
L	Н	L	Storing	Previous A inputs

<sup>‡</sup> Before LEAB low-to-high transition

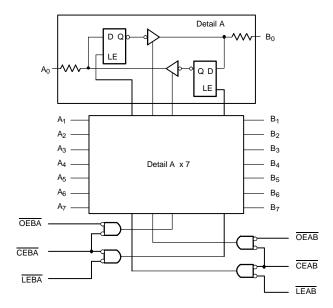
H = High logic level, L = Low logic level, X = Don't care,

A-to-B data flow shown; B-to-A is the same, except using CEBA, LEBA, and OEBA.



Z = High-impedance state

## functional block diagram



## absolute maximum rating over operating free-air temperature range (unless otherwise noted)†

Supply voltage range to ground potential	0.5 V to 7 V
DC input voltage range	0.5 V to 7 V
DC output voltage range	0.5 V to 7 V
DC output current (maximum sink current/pin)	120 mA
Package thermal impedance, $\theta_{JA}$ (see Note 1): Q package	61°C/W
SO package	46°C/W
Ambient temperature range with power applied, T <sub>A</sub>	–65°C to 135°C
Storage temperature range, T <sub>stg</sub>	65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## recommended operating conditions (see Note 2)

		MIN	NOM	MAX	UNIT
VCC	Supply voltage	4.75	5	5.25	V
VIH	High-level input voltage	2			V
V <sub>IL</sub>	Low-level input voltage			0.8	V
ІОН	High-level output current			-15	mA
loL	Low-level output current			12	mA
TA	Operating free-air temperature	-40		85	°C

NOTE 2: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation.



NOTE 1: The package thermal impedance is calculated in accordance with JESD 51-7.

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## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP <sup>†</sup>	MAX	UNIT
VIK	V <sub>CC</sub> = 4.75 V,			-0.7	-1.2	V	
Voн	$V_{CC} = 4.75 \text{ V},$	I <sub>OH</sub> = -15 mA		2.4	3.3		V
V <sub>OL</sub>	$V_{CC} = 4.75 \text{ V},$	I <sub>OL</sub> = 12 mA			0.3	0.55	V
R <sub>out</sub>	$V_{CC} = 4.75 \text{ V},$	$I_{OL} = 12 \text{ mA}$		20	25	40	Ω
V <sub>hys</sub>	All inputs				0.2		٧
ΊΗ	V <sub>CC</sub> = 5.25 V	$V_{IN} = V_{CC}$ $V_{IN} = 2.7 \text{ V}$				5 ±1	μА
I <sub>IL</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> = 0.5 V				±1	μΑ
lozh	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 2.7 V				15	μΑ
lozL	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 0.5 V				-15	μΑ
los <sup>‡</sup>	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 0 V	-60	-120	-225	mA	
l <sub>off</sub>	$V_{CC} = 0 V$	V <sub>OUT</sub> = 4.5 V			±1	μΑ	
ICC	$V_{CC} = 5.25 \text{ V},$	$V_{IN} \leq 0.2V$ ,	$V_{IN} \ge V_{CC} - 0.2 V$		0.1	0.2	mA
∆lCC	$V_{CC} = 5.25 \text{ V}, V_{IN} = 3.4 \text{ V}$ , f <sub>1</sub>	= 0, Outputs open			0.5	2	mA
ICCD¶	$\frac{V_{CC}}{CEAB} = 5.25 \frac{V}{O}$ One input switch CEAB and OEAB = LOW, CEB $V_{IN} \le 0.2 \text{ V or } V_{IN} \ge V_{CC} - 0.2 \text{ V}$	A = HIGH,	utputs open,		0.06	1.2	mA/ MHz
	V <sub>CC</sub> = 5.25 V, f <sub>0</sub> = 10 MHz,	One bit switching at f <sub>1</sub> = 5 MHz	$V_{IN} \le 0.2 \text{ V or}$ $V_{IN} \ge V_{CC} - 0.2 \text{ V}$		0.7	1.4	
l <sub>C</sub> #	Outputs open, CEAB and OEAB = LOW,	at 50% duty cycle	$V_{IN} = 3.4 \text{ V or GND}$		1.2	3.4	mA
IC.	$\overline{CEAB}$ and $\overline{OEAB} = \overline{LOW}$ , $\overline{CEBA} = \overline{HIGH}$ , $\overline{f_0} = \overline{LEAB} = 10 \text{ MHz}$	Eight bits switching at f <sub>1</sub> = 5 MHz	$V_{IN} \le 0.2 \text{ V or}$ $V_{IN} \ge V_{CC} - 0.2 \text{ V}$		2.8	5.6	
		at 50% duty cycle	$V_{IN} = 3.4 \text{ V or GND}$		5.1	14.6	
C <sub>i</sub>					5	10	pF
Co					9	12	pF

<sup>&</sup>lt;sup>†</sup> Typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

I<sub>C</sub> = Total supply current

I<sub>CC</sub> = Power-supply current with CMOS input levels

 $\Delta I_{CC}$  = Power-supply current for a TTL high input ( $V_{IN}$  = 3.4 V)

 $D_H$  = Duty cycle for TTL inputs high  $N_T$  = Number of TTL inputs at  $D_H$ 

ICCD = Dynamic current caused by an input transition pair (HLH or LHL)

f<sub>0</sub> = Clock frequency for registered devices, otherwise zero

f<sub>1</sub> = Input signal frequency

N<sub>1</sub> = Number of inputs changing at f<sub>1</sub>

All currents are in milliamperes and all frequencies are in megahertz.

Values for these conditions are examples of the ICC formula.



Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, IOS tests should be performed last.

<sup>§</sup> Per TTL-driven input (VIN = 3.4 V); all other inputs at VCC or GND

This parameter is derived for use in total power-supply calculations.

<sup>#</sup> I<sub>C</sub> = I<sub>CC</sub> +  $\Delta$ I<sub>CC</sub> × D<sub>H</sub> × N<sub>T</sub> + I<sub>CCD</sub> (f<sub>0</sub>/2 + f<sub>1</sub> × N<sub>1</sub>) Where:

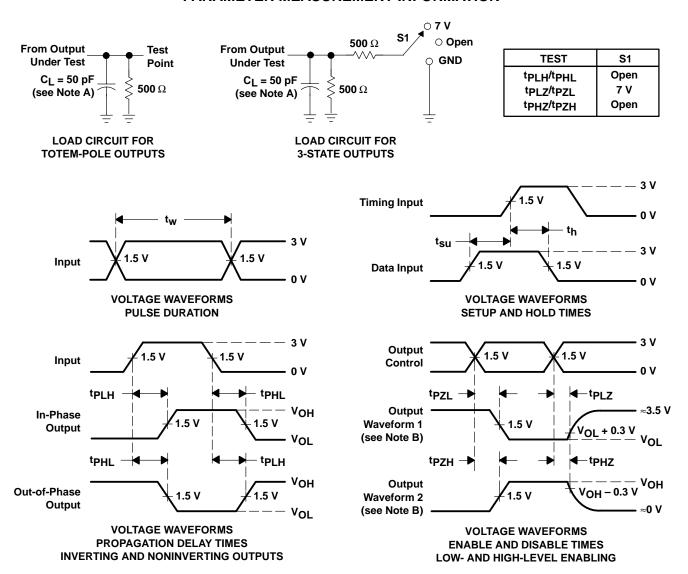
# timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

	DADA	METER	CY74FC	T2543T	CY74FCT	2543AT	CY74FCT	UNIT	
	FARA	WEIER	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
t <sub>W</sub> Pulse duration, LEBA or LEAB low					5		5		ns
t <sub>su</sub>	Setup time, high or low	low A or B before LEBA↓ or LEAB↓			2		2		ns
t <sub>h</sub>	Hold time, high or low A or B after LEBA↓ or LEAB↓		2		2		2		ns

## switching characteristics over operating free-air temperature range (see Figure 1)

PARAMETER	FROM	то	CY74FC	T2543T	CY74FCT	2543AT	CY74FCT	2543CT	UNIT
PARAMETER	(INPUT)	(OUTPUT)	(OUTPUT) MIN MAX MIN		MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> PLH	A or B	B or A	2.5	8.5	2.5	6.5	2.5	5.5	ns
<sup>t</sup> PHL	AOID	BOIA	2.0	0.5	2.0	0.5	2.0	3.3	115
<sup>t</sup> PLH	LEBA or LEAB	A or B	2.5	12.5	2.5	8	2.5	7	ns
<sup>t</sup> PHL	LEBA OI LEAD	AOIB	2.5 12.5		2.0	2.5 8		2.5 /	
<sup>t</sup> PZH	OEBA or OEAB	A or B	2	12	2	9	2	8	ns
t <sub>PZL</sub>	OEBA 01 OEAB	AOIB	2		2	9	2	8	110
<sup>t</sup> PZH	OFFIA OF A F	A or B	2	12	2	9	2	8	20
t <sub>PZL</sub>	CEBA or CEAB	AUIB	2	12	2	9	2	8	ns
<sup>t</sup> PHZ	<u> </u>	A D	2	9	2	7.5	2	6.5	
tPLZ	OEBA or OEAB	A or B	2	9	2	7.5	2	6.5	ns
<sup>t</sup> PHZ	CEBA or CEAB	A or B	2	9	2	7.5	2	6.5	ns
<sup>t</sup> PLZ	CEDA OF CEAB	AUIB	2	9	2	7.5	2	6.5	115

#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(0)
CY74FCT2543ATQCT	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT2543A
CY74FCT2543ATQCT.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT2543A
CY74FCT2543ATSOC	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT2543A
CY74FCT2543ATSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT2543A
CY74FCT2543CTQCT	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT2543C
CY74FCT2543CTQCT.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT2543C
CY74FCT2543CTQCTG4	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT2543C
CY74FCT2543CTQCTG4.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT2543C
CY74FCT2543CTSOC	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT2543C
CY74FCT2543CTSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT2543C

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



## **PACKAGE OPTION ADDENDUM**

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and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

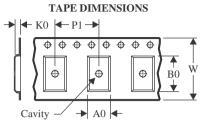
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT2543ATQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT2543CTQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT2543CTQCTG4	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

**PACKAGE MATERIALS INFORMATION** 

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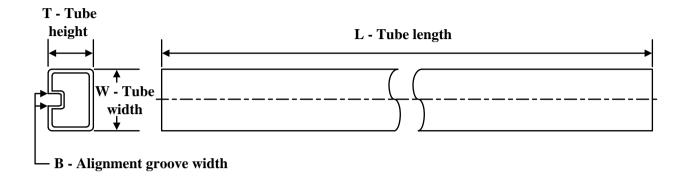
## \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT2543ATQCT	SSOP	DBQ	24	2500	353.0	353.0	32.0
CY74FCT2543CTQCT	SSOP	DBQ	24	2500	353.0	353.0	32.0
CY74FCT2543CTQCTG4	SSOP	DBQ	24	2500	353.0	353.0	32.0

## **PACKAGE MATERIALS INFORMATION**

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## **TUBE**

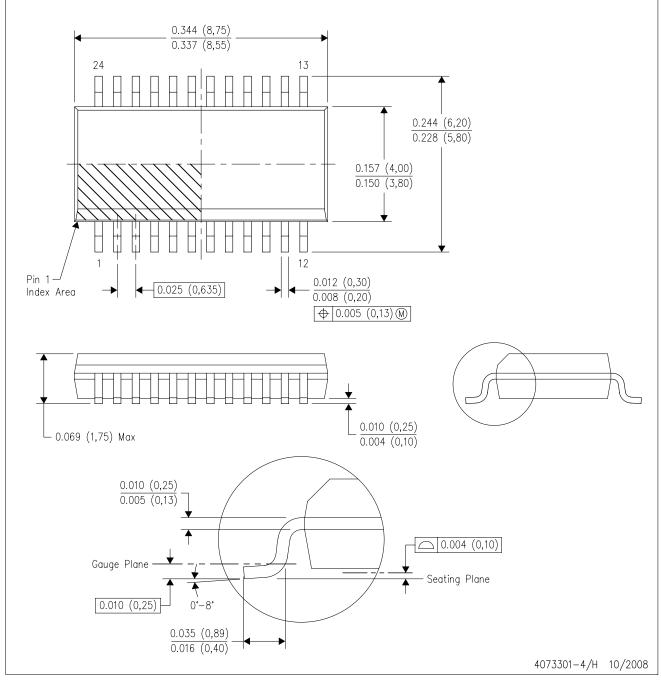


## \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CY74FCT2543ATSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT2543ATSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT2543CTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT2543CTSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

DBQ (R-PDSO-G24)

## PLASTIC SMALL-OUTLINE PACKAGE



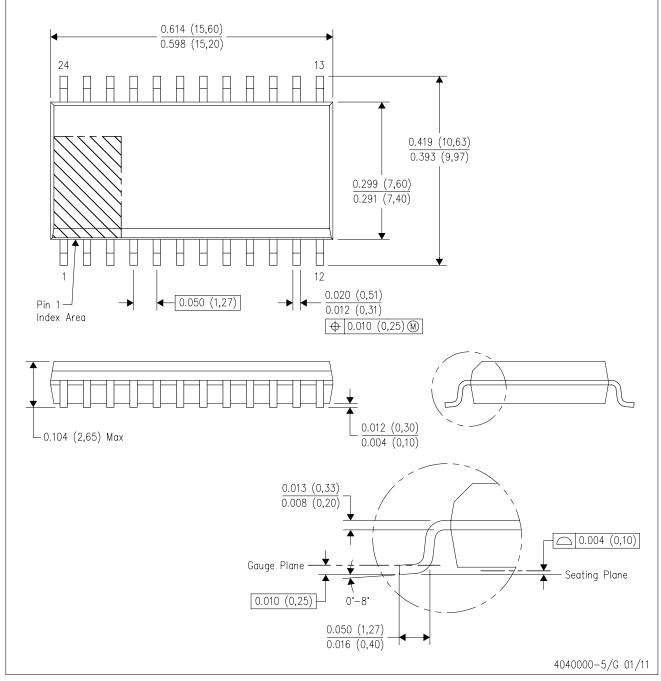
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
- D. Falls within JEDEC MO-137 variation AE.



DW (R-PDSO-G24)

## PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.



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